

REMARKS/ARGUMENTS

Claims 1, 3-9, 11-17 and 19-23 stand in the present application, claims 1, 4, 11 and 14 having been amended. Reconsideration and favorable action is respectfully requested in view of the above amendments and the following remarks.

Claims 1, 3-4, 6-9, 14-19 and 21 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Kawagoe in view of Norihiro, and further in view of Paoli; claim 5 is rejected under 35 U.S.C. § 103(a) as being unpatentable over Kawagoe in view of Norihiro and Paoli and further in view of Komori; claims 11-13 and 20 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Kawagoe in view of Paoli and further in view of Nagashima; and claims 22-23 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Kawagoe, Norihiro and Paoli and further in view of Chen in view of Morse. Applicants respectfully traverse all of the Examiner's § 103 rejections of the claims.

Amended claims 1, 4, 11 and 14 are supported by the present application at, *inter alia*, Figs. 2B, 9, 10, etc. and the corresponding accompanying text of the present specification. More specifically, in the amended claims, the semiconductor stacked structure is described as defining, when viewed in plan, a quadrangle having four right angles and having a first edge, a second edge opposing the first edge, a third short edge and a fourth short edge opposing the third short edge. The striped waveguide is described as extending parallel to the first/second edges of the quadrangle. The insulative region (claims 1 and 4), the region for reducing the capacitance of the element (claim 11) or the insulation region for reducing the capacitance of the element (claim 14) is described as defining a rectangle when viewed in plan, the rectangle

having a first long edge extending parallel to a longitudinal direction of the striped waveguide region, a second long edge opposing the first long edge and positioned nearer to the striped waveguide region than the first long edge, a first short edge and a second short edge opposing the first short edge, with the first short edge being positioned nearer to the third short edge being positioned nearer to the third short edge of the quadrangle than the second short edge, wherein the first long edge of the rectangle is remote from the edge of the quadrangle, and the first and second short edges of the rectangle are remote from the third short and fourth short edges of the quadrangle, respectively.

None of the cited references taken singly or in any combination teach or suggest that the short edges of the rectangle (insulative region, insulation region or region for reducing the capacitance of the element) are remote from the third and fourth short edges of the quadrangle (semiconductor stacked structure). All of the cited references are silent about edges corresponding to the short edges of the rectangle (insulative region, insulation region or region for reducing the capacitance of the element).

Therefore, in view of the above amendments and remarks, it is respectfully requested that the application be reconsidered and that all of claims 1, 3-9, 11-17 and 19-23, standing in the application, be allowed and that the case be passed to issue. If there are any other issues remaining which the Examiner believes could be resolved through either a supplemental response or an Examiner's amendment, the Examiner is respectfully requested to contact the undersigned at the local telephone exchange indicated below.

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Respectfully submitted,

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By: _____



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